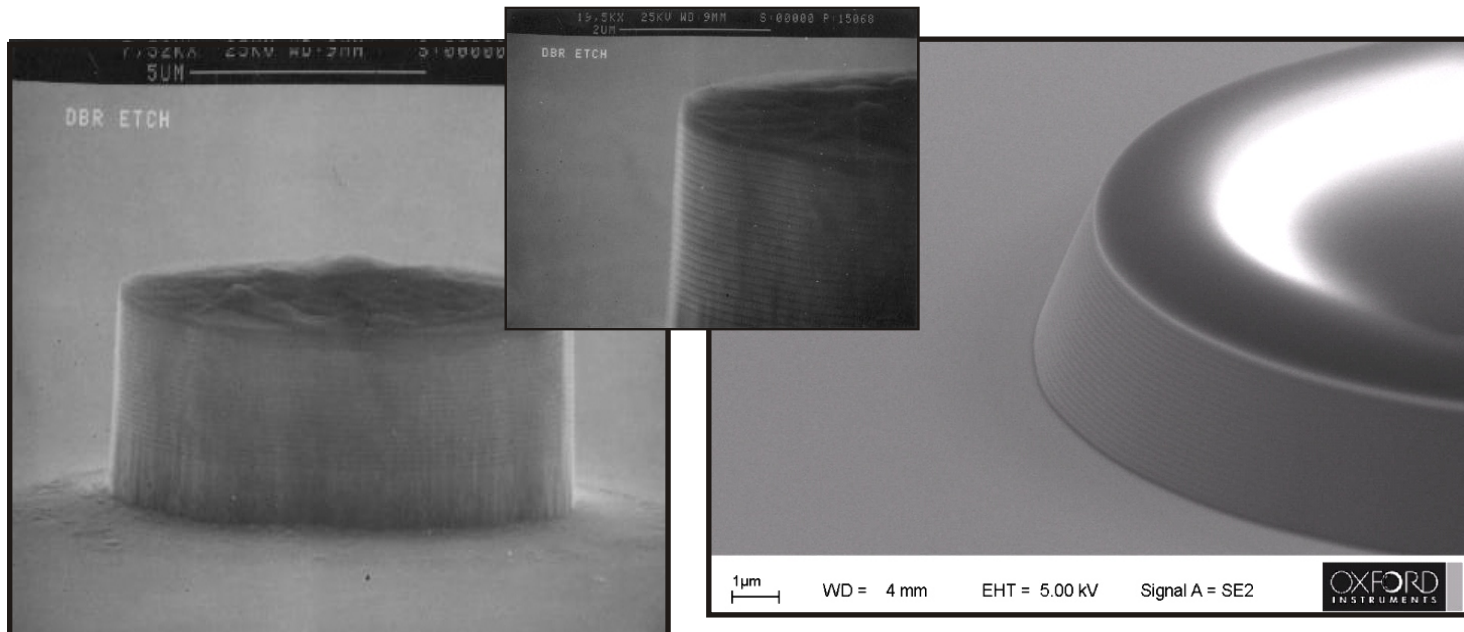


# Plasmalab Data

## ICP RIE: GaAs/ AlGaAs DBR Heterostructures

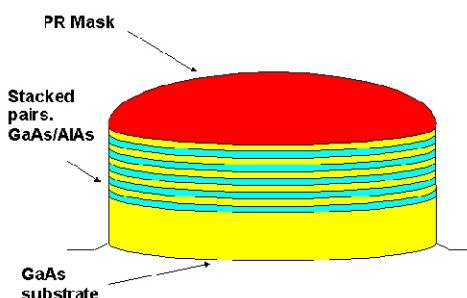
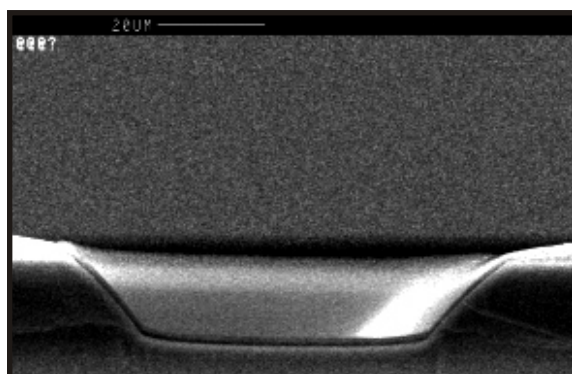
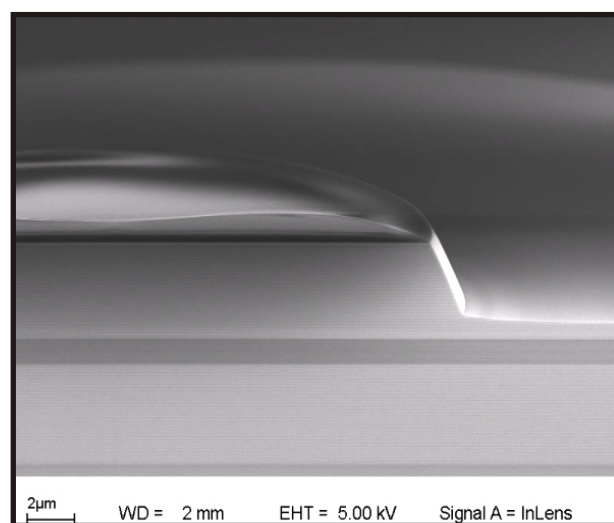
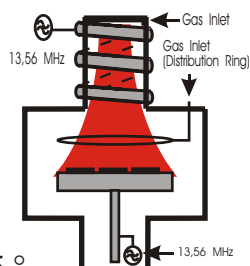


DBR Heterostructures  
 6 µm deep anisotropic  
 GaAs/ AlGaAs Etch

*Plasmalab 80 Plus*  
*Plasmalab System 100*  
*Plasmalab System 133*

Heterostructures: 0.3 - 1 µm/ min  
 selectivity to PR Mask > 3 : 1,  
 to SiO<sub>2</sub> > 10 : 1  
 (for high rate anisotropic etching)  
 low bias process or low substrate damage  
 profile controllable for sloped walls: 55 - 75 °  
 selectivity to PR: 5 - 10 : 1 at > 100 nm/ min

3 µm deep etch  
 with sloped wall  
 very smooth sidewalls



sloped wall 10 µm deep GaAs/ AlGaAs etch